CERTIFICATE OF MAILING

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12-2703

Signature:

ITE: Kellecot A Boumann

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PATENT
Attorney Docket No. NTI-019-2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application)	PATENT APPLICATION	<u>N</u>		
Inventor(s): Christophe Pierrat et al.)	Art Unit: 2812	-	<u> </u>	
Application No.: 09/675,197)	· · · · · · · · · · · · · · · · · · ·	5		
Filed: 09/29/2000)	Examiner: unknown	ECHWOLOGY	Nob I	REC
Title Dissection Of Edges With Projection Points In A Fabrication Layout For Correcting Proximity Effects)	# . -	CENTER	7 2002	EIVED
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INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

Listed below or on an attached Form PTO-1449 is information known to applicant(s). A copy of each listed publication and U.S. and foreign patent, except for pending U.S. applications, is being submitted herewith, along with a concise explanation of information in a foreign language, if any, pursuant to 37 C.F.R. §1.97-1.98.

Applicants respectfully request that the listed information be considered by the Examiner and be made of record in the above-identified application. If form PTO-1449 is enclosed, the Examiner is requested to initial and return it in accordance with MPEP § 609.

This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56.

\boxtimes	This st	atement	qualifies under 37 C.F.R. § 1.9	7, subsection (b) because (check all that apply):
		(1)	It is being filed within 3 mont prosecution application OR	hs of the application filing date and is other than a continued on under § 1.53(d)
		(2)	It is being filed within 3 mont	hs of entry of a national stage
	\boxtimes	(3)	•	il date of the first Office Action on the merits.
		(4)	OR – It is being filed before the man continued examination	iling of a first Office Action after the filing of a request for n under § 1.114
	date of	the earl		filed after the period specified in § 1.97(b), but before the mailing r § 1.113, a notice of allowance under § 1.311, or an action that n, then:
		a certit	fication as specified in § 1.97(e)	is provided below; or
			of \$180.00 as set forth in § 1.17(coapers filed together with this st	p) is authorized below, enclosed, or included with the payment of atement.
			97(d). If this statement is being a sissue fee, then:	filed after the period specified in § 1.97(c), but on or before
	A.	a certi	fication as specified in § 1.97(e)	is completed below; and
	B.		of \$180.00 as set forth in § 1.17(coapers filed together with this st	p) is authorized below, enclosed, or included with the payment of atement.
	charge	any add		by authorized to charge the above-referenced fees of \$ 180 and ayment associated with this communication to Deposit Account
				Respectfully submitted,
				BEVER, HOFFMAN & HARMS, LLP
Dated:	4	- //	02	By: Jeanette S. Harms, Reg. No. 35,537
	one: (40 ner No. 1	98) 451-: 29477	5900	11211010 0. 1121110, 1146. 110. 00,007



INFORMATION DISCLOSURE CITATION

PTO-1449

Atty. Docket No.

Serial No.

NTI-019-2

09/675,197

Applicant

PIERRAT, Christophe

Filing Date

Group

9/29/2000

2812

ILS PATENT DOCUMENTS

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EXAMINER:	Date Considered:	

			Atty. Docket No.	Seria	l No.		
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	CITATION		Applicant				
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* MADEMARY	ngg.	FO	REIGN PATENT DOCU	JMENTS			
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EXAMINER:	Date Considered:	

INFORMATION DISCLOSURE
CITATION

PTO-1449

Atty. Docket No.

Serial No.

NTI-019-2

09/675,197

Applicant

PIERRAT, Christophe

Filing Date

Group

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EXAMINER:	Date Considered:	190	
EXAMINER: Initial if reference considered, wheth MPEP § 609; draw line through citation if not in copy of this form with next communication to app	onformance and not considered. Include	CENTER 2800	Only: 711; 24; 1

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